

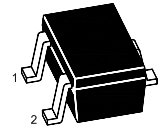
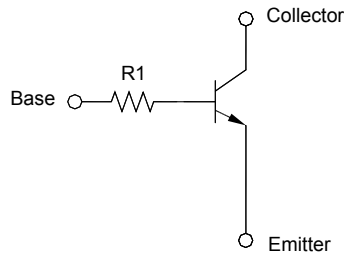
MMDTC323W

NPN Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



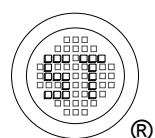
1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	15	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	100	-	600	-
Collector Base Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	-	0.5	μA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	-	0.5	μA
Collector Base Breakdown Voltage at $I_C = 50\text{ }\mu\text{A}$	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	15	-	-	V
Emitter Base Breakdown Voltage at $I_E = 50\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 50\text{ mA}$, $I_B = 2.5\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Input Resistor	R_1	1.64	2.2	2.86	K Ω
Transition Frequency at $V_{CE} = 10\text{ V}$, $-I_E = 50\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	200	-	MHz



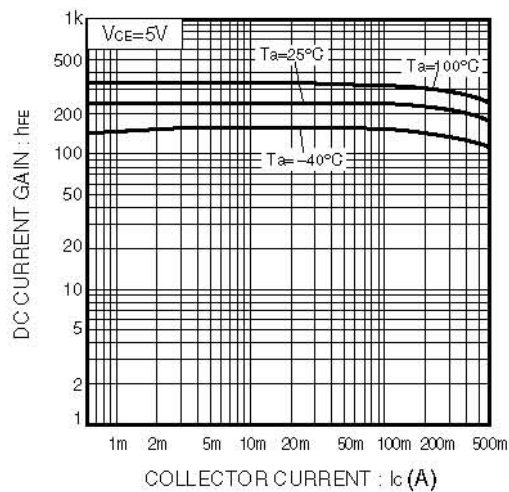


Fig.1 DC current gain vs. Collector current

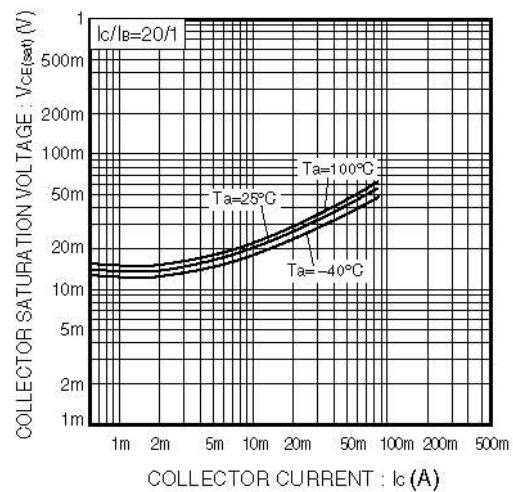


Fig.2 Collector-emitter saturation voltage vs. Collector current

